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SOT-89 P Silicon PNP transistor in a SOT-89 Plastic Package.

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2SD2185

Low $V_{CE(sat)}$, complementary to 2SD2185.

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For low frequency output amplification.

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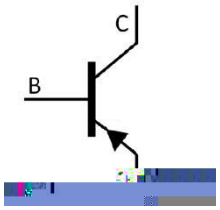

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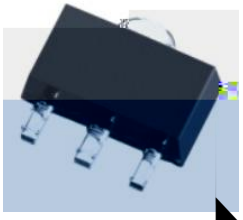

PIN1 Base I 2 Collector PIN 3 Emitter

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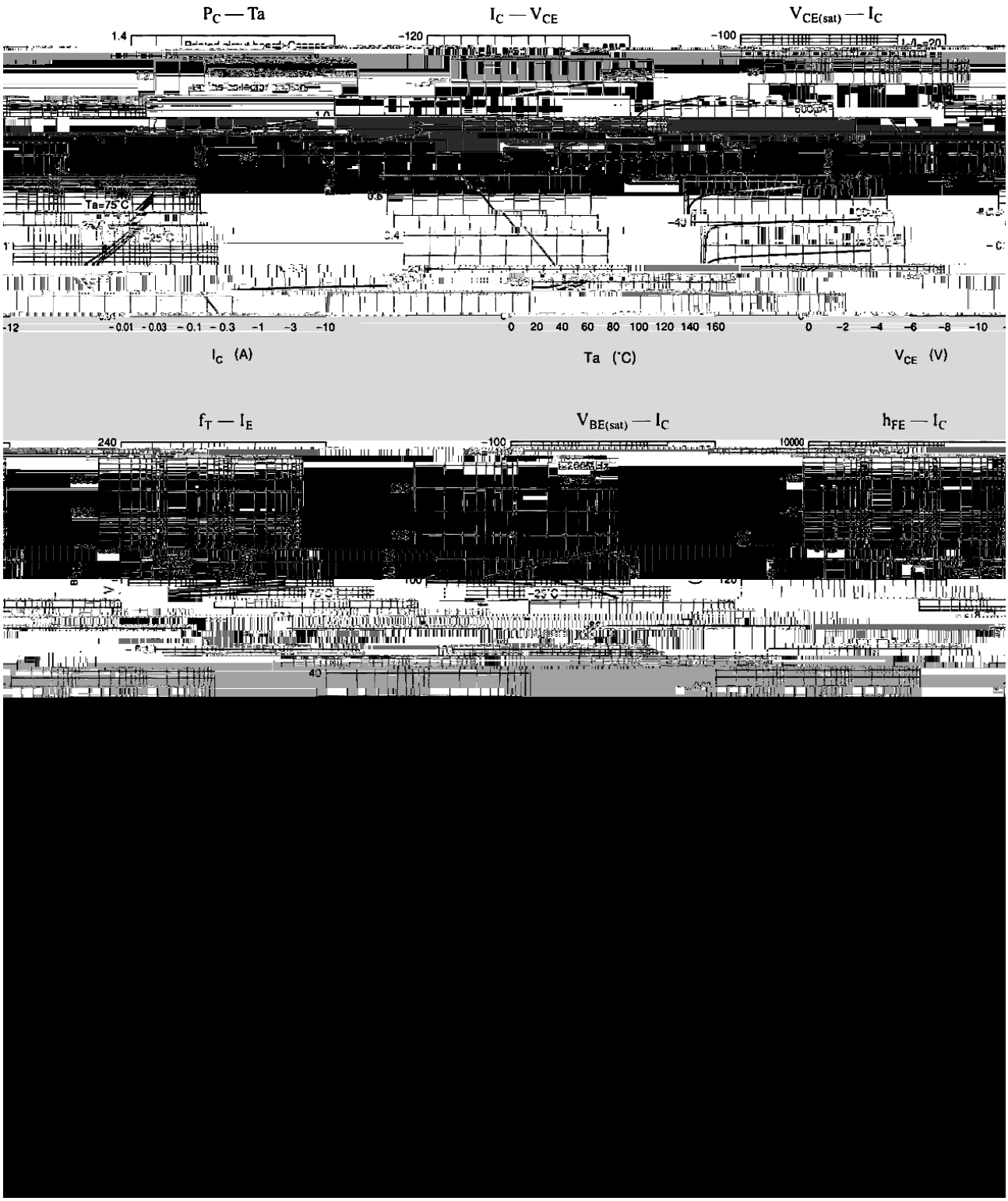
h_{FE} Classifications Symbol	R	S
h_{FE} Range	120 240	170 340
Marking	H1IR ⁑	H1IS ⁑

	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-2.0	A
Collector Current -Continuous(Pulse)	I_{CP}	-3.0	A
Collector Power Dissipation*	*P_C	1.0	W
Junction Temperature	T_j	150	


P_C — Ta
I_C — V_{CE}
$V_{CE(sat)}$ — I_C
Ta=75°C
25°C
-25°C
I_C (A)
Ta (°C)
V_{CE} (V)
f_T — I_E
$V_{BE(sat)}$ — I_C
h_{FE} — I_C

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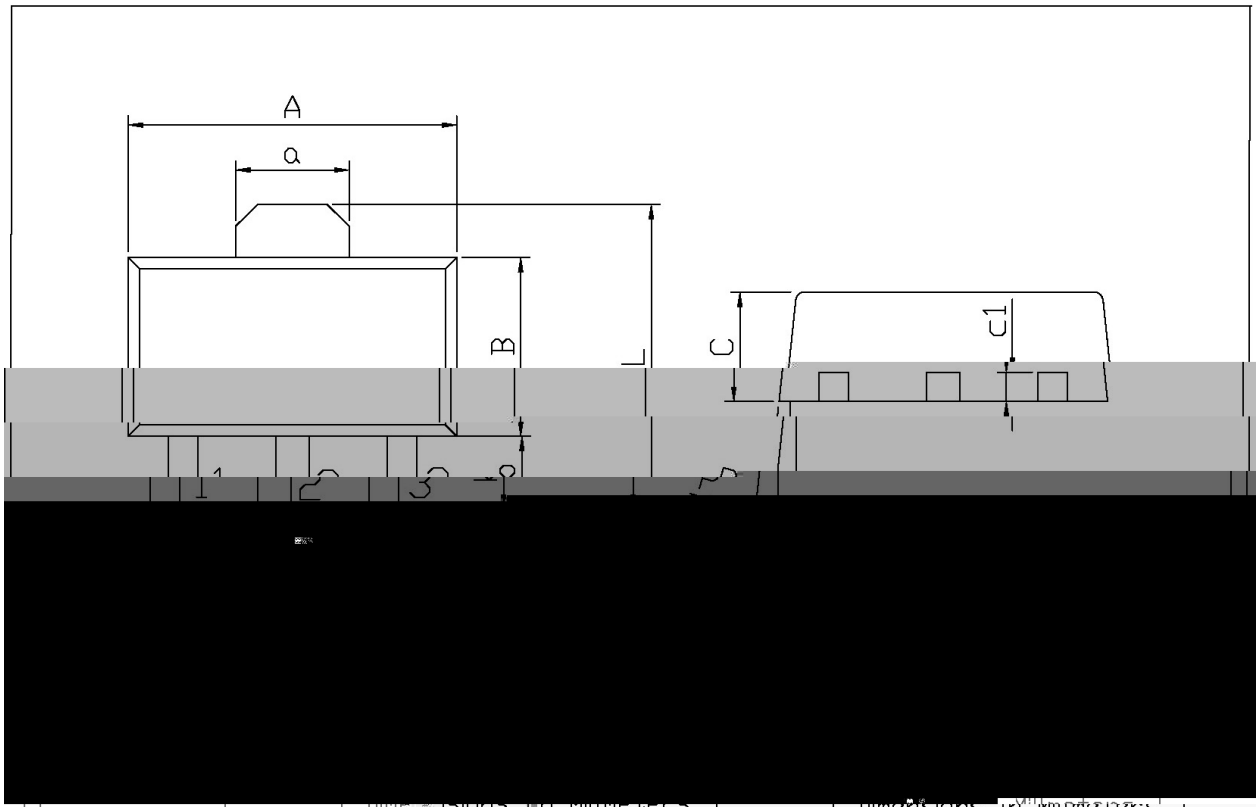
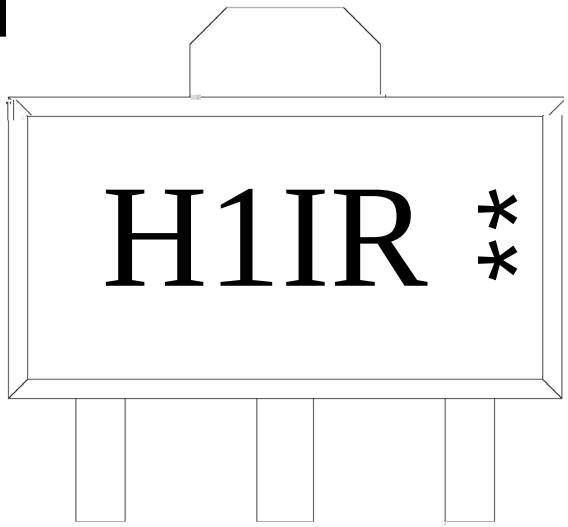
SOT-89

单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.4	4.7	a1	0.36	0.56
B	2.35	2.65	a2	0.30	0.50
b	3.878	4.478	c	1.40	1.70



H

1I

R: h_{FE}

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Note:

H: Company Code.

1I: Product Type.

R: h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

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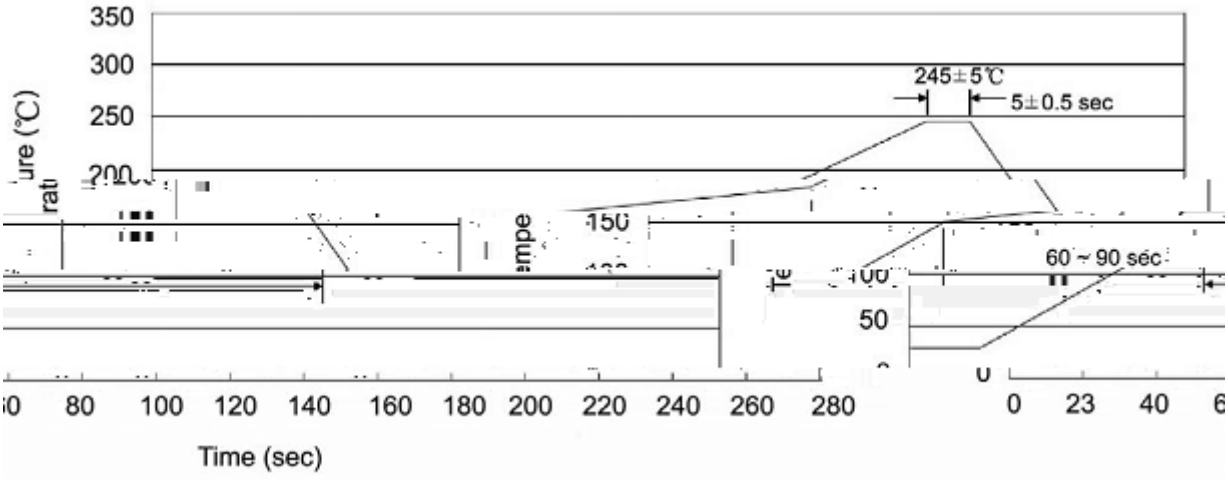

Note:

1 25 150 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

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260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

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/ REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

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